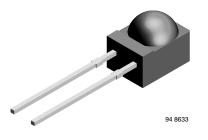
Vishay Semiconductors



RoHS

COMPLIANT

Silicon PIN Photodiode, RoHS Compliant



FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (in mm): 4.5 x 5 x 6
- Radiant sensitive area (in mm²): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- · Fast response times
- Angle of half sensitivity: $\phi = \pm 60^{\circ}$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- · High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSALxxxx series IR emitters

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.5} (nm)	
BPV22F	80	± 60	870 to 1050	

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
BPV22F	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	60	V	
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	215	mW	
Junction temperature		Тj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \le 5 s$	T _{sd}	260	°C	
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	350	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

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BPV22F is a PIN photodiode with high speed and high radiant sensitivity in a black, plastic package with side view lens and daylight blocking filter. Filter bandwdith is matched with 900 nm to 950 nm IR emitters. The lens achieves 80 % of sensitivity improvement in comparison with flat package.



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PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	60			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		2	30	nA
Diode capacitance	V _R = 0 V, f = 1 MHz, E = 0	CD		70		pF
Serial resistance	V _R = 12 V, f = 1 MHz	R _S		400		Ω
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	Vo		370		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	l _k		75		μΑ
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_R = 5 \text{ V}$	I _{ra}	55	80		μΑ
Temperature coefficient of Ira	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_R = 10 \text{ V}$	TK _{Ira}		0.1		%/K
Absolute spectral sensitivity	$V_{R} = 5 V, \lambda = 870 nm$	s(λ)		0.35		A/W
	$V_{\rm R} = 5 V, \lambda = 950 \text{nm}$	s(λ)		0.6		A/W
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λρ		950		nm
Range of spectral bandwidth		λ _{0.5}		870 to 1050		nm
Quantum efficiency	$\lambda = 950 \text{ nm}$	η		90		%
Noise equivalent power	$V_{R} = 10 V, \lambda = 950 nm$	NEP		4 x 10 ⁻¹⁴		W/√ Hz
Detectivity	$V_{R} = 10 V, \lambda = 950 nm$	D*		6 x 10 ¹²		cm√Hz/W
Rise time	V_{R} = 10 V, R _L = 1 kΩ, λ = 820 nm	t _r		100		ns
Fall time	V_R = 10 V, R_L = 1 k Ω , λ = 820 nm	t _f		100		ns
Cut-off frequency	V_R = 12 V, R_L = 1 k Ω , λ = 870 nm	f _c		4		MHz
	$V_{B} = 12 V, R_{L} = 1 k\Omega, \lambda = 950 nm$	f _c		1		MHz

Note

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BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

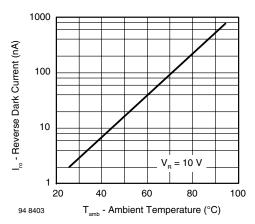


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

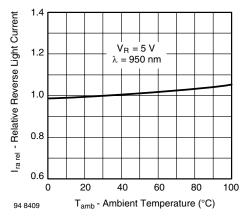


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

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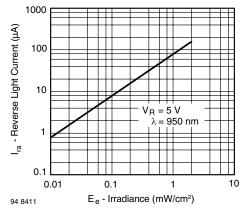


Fig. 3 - Reverse Light Current vs. Irradiance

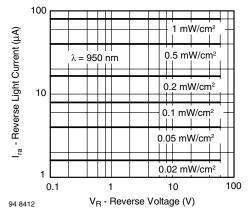


Fig. 4 - Reverse Light Current vs. Reverse Voltage

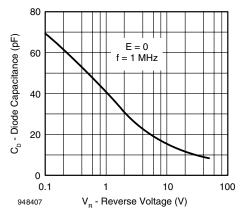


Fig. 5 - Diode Capacitance vs. Reverse Voltage

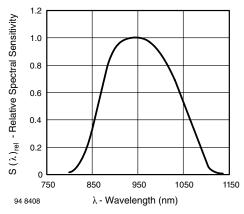


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

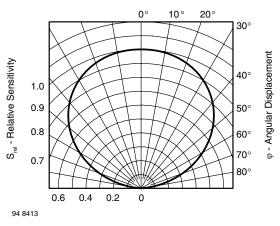


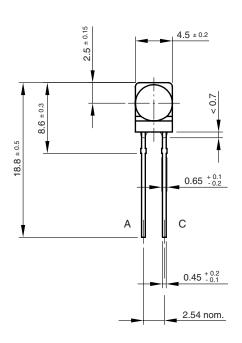
Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

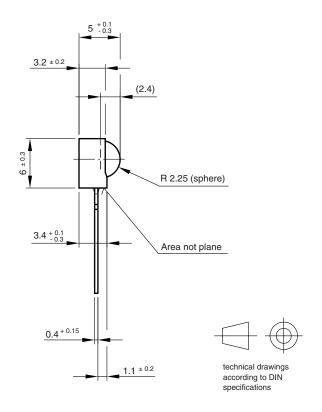


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PACKAGE DIMENSIONS in millimeters





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